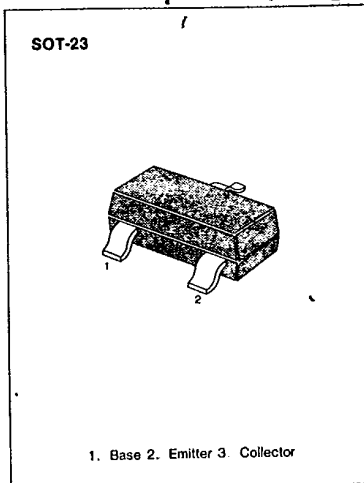


MMBA811C7**PNP EPITAXIAL SILICON TRANSISTOR****DRIVER TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)**

| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-Base Voltage | V _{CB0} | 50 | V |
| Collector-Emitter Voltage | V _{CEO} | 45 | V |
| Emitter-Base Voltage | V _{EB0} | 5 | V |
| Collector Current | I _C | 50 | mA |
| Collector Dissipation | P _C | 350 | mW |
| Storage Temperature | T _{stg} | 150 | °C |

• Refer to MMBT5086 for graphs

**ELECTRICAL CHARACTERISTICS (T_a = 25°C)**

| Characteristic | Symbol | Test Condition | Min | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|------|
| Collector-Base Breakdown Voltage | BV _{CB0} | I _C = 100μA, I _E = 0 | 50 | | V |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | I _C = 1.0mA, I _B = 0 | 45 | | V |
| Emitter-Base Breakdown Voltage | BV _{EB0} | I _E = 10μA, I _C = 0 | 5 | | V |
| Collector Cutoff Current | I _{CB0} | V _{CB} = 40V, I _E = 0 | | 50 | nA |
| Emitter Cutoff Current | I _{EB0} | V _{EB} = 5.0V, I _C = 0 | | 50 | nA |
| DC Current Gain | h _{FE} | V _{CE} = 3V, I _C = 0.1mA | 150 | | |
| | | V _{CE} = 3V, I _C = 0.5mA | 300 | 600 | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C = 20mA, I _B = 2.0mA | | 0.3 | V |
| Current Gain-Bandwidth Product | f _T | I _C = 1.0mA, V _{CE} = 6.0V f = 100MHz | 75 | | MHz |

Marking